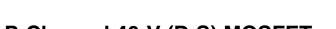
Vishay Siliconix





# P-Channel 40-V (D-S) MOSFET

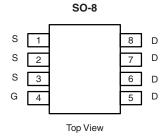
PRODUCT SUMMARY						
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ.)			
- 40	$0.014 \text{ at V}_{GS} = -10 \text{ V}$	- 10.5	40			
	0.021 at V <sub>GS</sub> = - 4.5 V	- 8.7	40			

### **FEATURES**

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Power MOSFET
- 100 % R<sub>g</sub> Tested
- Compliant to RoHS Directive 2002/95/EC

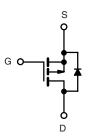


ROHS COMPLIANT HALOGEN FREE



Ordering Information: Si4401BDY-T1-E3 (Lead (Pb)-free)

Si4401BDY-T1-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	T <sub>A</sub> = 25 °C, unle	ss otherwise i	noted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V <sub>DS</sub>	- 40		
Gate-Source Voltage		V <sub>GS</sub>	± 20		V
Out in the Comment (T. 150.00)3	T <sub>A</sub> = 25 °C	- I <sub>D</sub>	- 10.5	- 8.7	
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 70 °C		- 8.3	- 5.9	
Pulsed Drain Current		I <sub>DM</sub>	- 50		Α
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	- 2.6	- 1.36	
Avalanche Current	L = 1 mH	I <sub>AS</sub>	30		
Single Pulse Avalanche Energy	L=IIIII	E <sub>AS</sub>		45	mJ
M ·	T <sub>A</sub> = 25 °C	P <sub>D</sub>	2.9	1.5	W
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C		1.85	0.95	
Operating Junction and Storage Temperature Ra	T <sub>J</sub> , T <sub>stg</sub>	- 55	to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Manipular landing to Austriant	t ≤ 10 s	R <sub>thJA</sub>	36	43	°C/W
Maximum Junction-to-Ambient <sup>a</sup>	Steady State		70	84	
Maximum Junction-to-Foot (Drain)	Steady State	$R_{thJF}$	16	21	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

# Vishay Siliconix



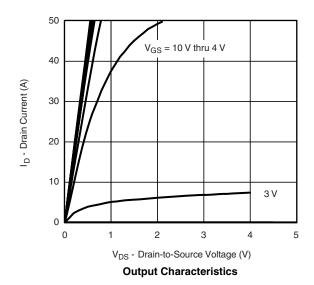
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static	-						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = - 250 μA - 1			- 3.0	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zana Cata Maltana Busin Comment		V <sub>DS</sub> = - 40 V, V <sub>GS</sub> = 0 V		-1			
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = -40 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 70 ^{\circ}\text{C}$			- 10	μΑ	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = - 5 V, V <sub>GS</sub> = - 10 V	- 30			Α	
5	D	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 10.5 A		0.011	0.014	0	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 8.7 A		0.0165	0.021	Ω	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 10.5 A		26		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	I <sub>S</sub> = - 2.7 A, V <sub>GS</sub> = 0 V		- 0.74	- 1.1	V	
Dynamic <sup>b</sup>							
Total Gate Charge	$Q_g$			40	55		
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -15 \text{ V}, V_{GS} = -5 \text{ V}, I_{D} = -10.5 \text{ A}$		10		nC	
Gate-Drain Charge	$Q_{gd}$			14			
Gate Resistance	$R_g$		1.4	2.8	4.2	Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			16	25		
Rise Time	t <sub>r</sub>	$V_{DD}$ = - 15 V, $R_L$ = 15 $\Omega$		15	25		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D\cong$ - 1 A, $V_{GEN}=$ - 10 V, $R_g=$ 6 $\Omega$		97	150	ns	
Fall Time	t <sub>f</sub>			47	75		
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = - 2.1 A, dl/dt = 100 A/μs		35	55		

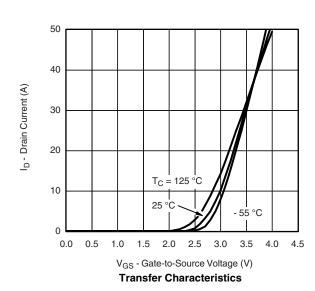
#### Notes:

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



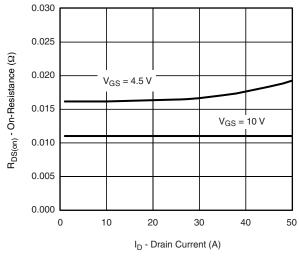




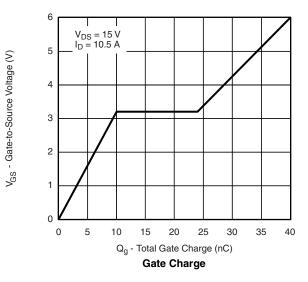


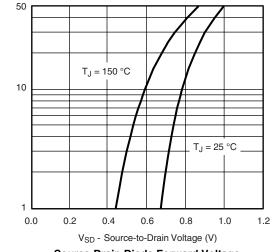


## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

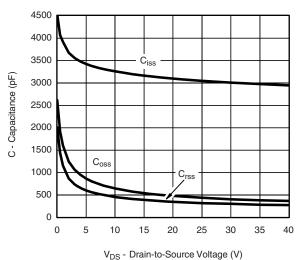


### On-Resistance vs. Drain Current

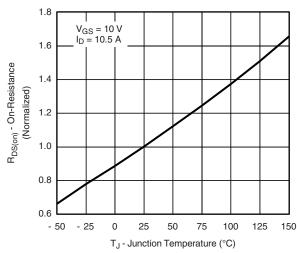




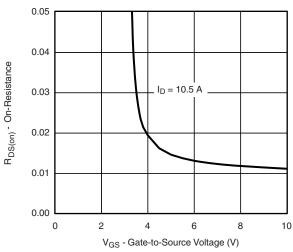
Source-Drain Diode Forward Voltage



Capacitance



On-Resistance vs. Junction Temperature



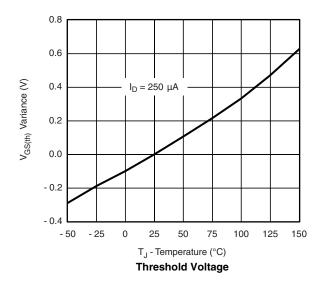
On-Resistance vs. Gate-to-Source Voltage

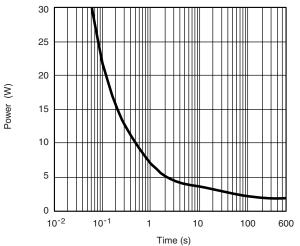
I<sub>S</sub> - Source Current (A)

# Vishay Siliconix

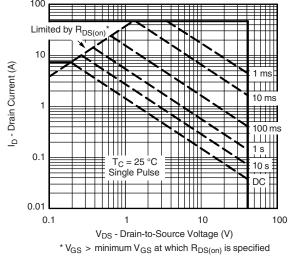
# VISHAY.

## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

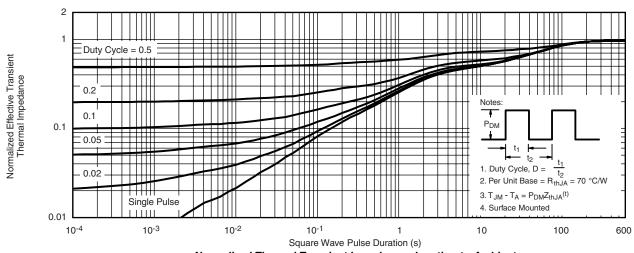




Single Pulse Power, Junction-to-Ambient



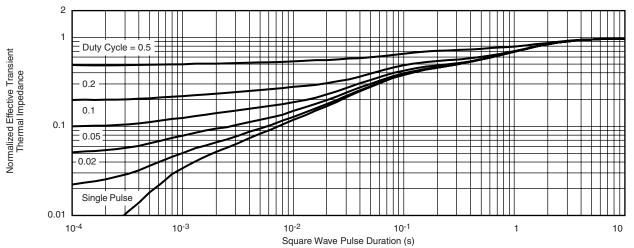




Normalized Thermal Transient Impedance, Junction-to-Ambient



## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?73140">www.vishay.com/ppg?73140</a>.



SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







MILLIMETERS			INC	NCHES		
DIM	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
A <sub>1</sub>	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
Е	3.80	4.00	0.150	0.157		
е	1.27 BSC		0.050	50 BSC		
Н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
ECN: C-06527-Rev. I. 11-Sep-06						

DWG: 5498

Document Number: 71192 www.vishay.com 11-Sep-06



### **RECOMMENDED MINIMUM PADS FOR SO-8**



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index

Ш



## **Legal Disclaimer Notice**

Vishay

## **Disclaimer**

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Revision: 13-Jun-16 1 Document Number: 91000

# **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by Vishay manufacturer:

Other Similar products are found below:

614233C 648584F IRFD120 JANTX2N5237 2N7000 FCA20N60\_F109 FDZ595PZ 2SK2545(Q,T) 405094E 423220D

TPCC8103,L1Q(CM MIC4420CM-TR VN1206L 614234A 715780A NTNS3166NZT5G SSM6J414TU,LF(T 751625C

IPS70R2K0CEAKMA1 BUK954R8-60E DMN3404LQ-7 NTE6400 SQJ402EP-T1-GE3 2SK2614(TE16L1,Q) 2N7002KW-FAI

DMN1017UCP3-7 EFC2J004NUZTDG ECH8691-TL-W FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE221 NTE2384

NTE2903 NTE2941 NTE2945 NTE2946 NTE2960 NTE2967 NTE2969 NTE2976 NTE455 NTE6400A NTE2910 NTE2916 NTE2956

NTE2911 US6M2GTR TK10A80W,S4X(S SSM6P69NU,LF